

WSF28N06

N-Ch MOSFET

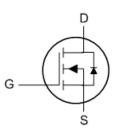
Features

- 60V/28A,
 - $\begin{array}{l} \mathsf{R}_{\mathrm{DS(ON)}} = 28\mathrm{m}\Omega \ (\mathsf{TYP.}) \textcircled{0} \mathsf{V}_{\mathrm{GS}} = 10\mathsf{V} \\ \mathsf{R}_{\mathrm{DS(ON)}} = 38\mathrm{m}\Omega \ (\mathsf{TYP.}) \textcircled{0} \mathsf{V}_{\mathrm{GS}} = 5\mathsf{V} \end{array}$
- · Reliable and Rugged
- Lead Free and Green Devices Available
 (RoHS Compliant)
- 100% UIS + R_a Tested

Pin Configuration



Top View of TO-252-2



Applications

- Switching Application for Actuator.
- Converter Application in LED TV.
- Switching Application in Industry.

N-Channel MOSFET

Absolute Maximum Ratings ($T_A = 25^{\circ}C$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit	
Common	Ratings			•
V _{DSS}	Drain-Source Voltage		60	V
V _{GSS}	Gate-Source Voltage		±20	
TJ	Maximum Junction Temperature		175	°C
T _{STG}	Storage Temperature Range		-55 to 175	°C
ls	Diode Continuous Forward Current	T _C =25°C	12	A
	Pulse Drain Current Tested	T _c =25°C	96	— A
I _{DP}		T _c =100°C	68	
	Continuous Drain Current	T _c =25°C	28	— A
I _D		T _c =100°C	17	
P _D	Maximum Power Dissipation	T _c =25°C	60	— w
		T _c =100°C	30	
$R_{ ext{ hetaJC}}$	Thermal Resistance-Junction to Case		2.5	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance-Junction to Ambient		50	°C/W
E _{AS}	Drain-Source Avalanche Energy	L=0.5mH	22	mJ



Electrical Characteristics ($T_A = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit	
Static Cha	aracteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	60	-	-	V	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V, V _{GS} =0V	-	-	1		
		T _J =125°C	-	-	30	μA	
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1	2	3	V	
I _{GSS}	Gate Leakage Current	V _{GS} =±16V, V _{DS} =0V	-	-	±10	μΑ	
D a	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =12A	-	28	40	mΩ	
$R_{DS(ON)}$ a		V _{GS} =5V, I _{DS} =11A	-	38	50		
Diode Cha	aracteristics						
V_{SD}^{a}	Diode Forward Voltage	I _{SD} =12A, V _{GS} =0V	-	0.8	1.3	V	
trr	Reverse Recovery Time		-	30	-	ns	
Q _{rr}	Reverse Recovery Charge	-I _{DS} =12A, dl _{SD} /dt=100A/μs	-	35	-	nC	
Dynamic	Characteristics ^b				•		
C _{iss}	Input Capacitance	V _{GS} =0V,	-	530	-		
Coss	Output Capacitance	V _{DS} =30V,	-	85	-	pF	
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz	-	40	-	1	
t _{d(ON)}	Turn-on Delay Time		-	8	15		
Tr	Turn-on Rise Time	V _{DD} =30V, R _L =30Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	8	15		
$t_{d(OFF)}$	Turn-off Delay Time		-	28	51	ns	
T _f	Turn-off Fall Time		-	22	41		
Gate Cha	rge Characteristics ^b						
Qg	Total Gate Charge		-	12	17		
Q_{gs}	Gate-Source Charge	V _{DS} =30V, V _{GS} =10V, I _{DS} =12A	-	3	-	nC	
Q_{gd}	Gate-Drain Charge		-	3	-		

Note a : Pulse test ; pulse width \leq 300 μ s, duty cycle \leq 2%.

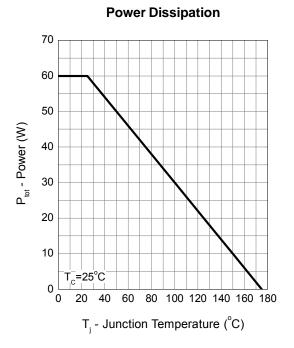
Note b : Guaranteed by design, not subject to production testing.



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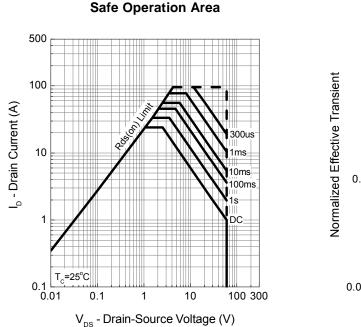
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Typical Operating Characteristics

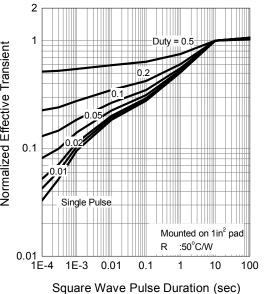


 f_{i} - Junction Temperature (°C)

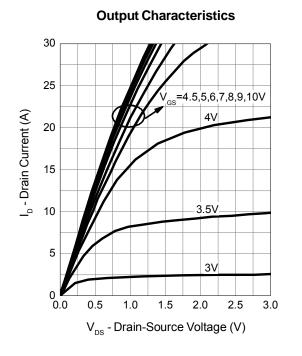
Drain Current



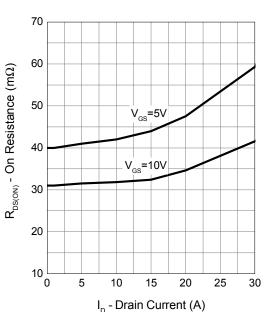
Thermal Transient Impedance







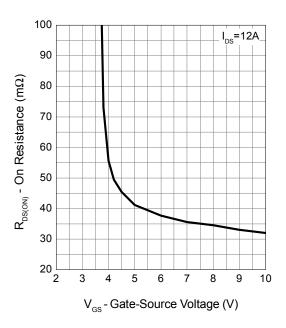
Typical Operating Characteristics (Cont.)

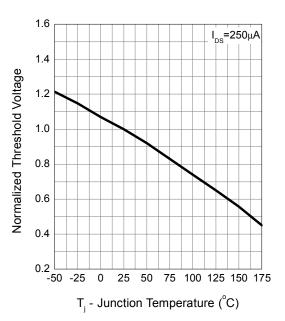


Drain-Source On Resistance

Gate-Source On Resistance

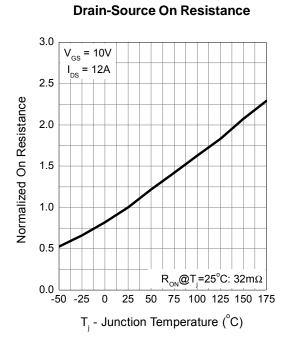
Gate Threshold Voltage

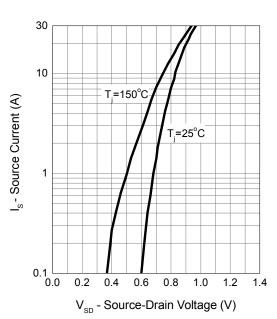






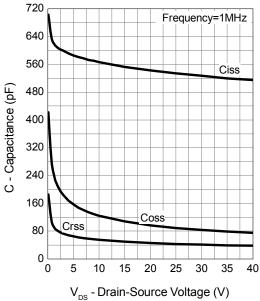
Typical Operating Characteristics (Cont.)



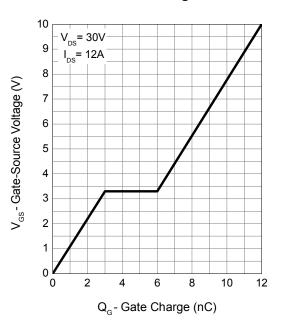


Source-Drain Diode Forward

Capacitance



Gate Charge

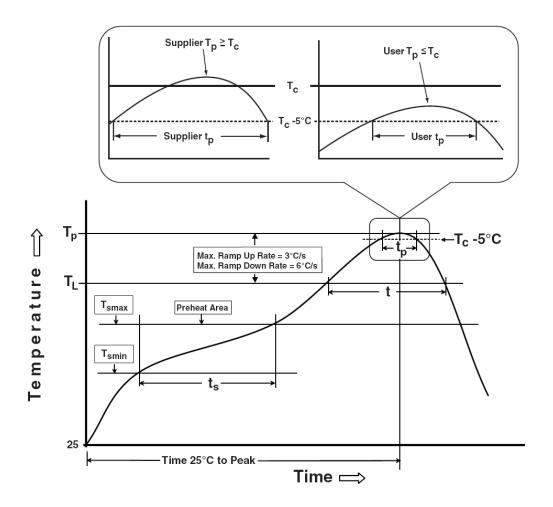




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Classification Profile





Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly	
$\begin{array}{c} \textbf{Preheat \& Soak} \\ \textbf{Temperature min } (\textbf{T}_{smin}) \\ \textbf{Temperature max } (\textbf{T}_{smax}) \\ \textbf{Time } (\textbf{T}_{smin} \text{ to } \textbf{T}_{smax}) \ (\textbf{t}_{s}) \end{array}$	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds	
Average ramp-up rate (T _{smax} to T _P)	3 °C/second max.	3°C/second max.	
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds	
Peak package body Temperature (T _p)*	See Classification Temp in table 1	See Classification Temp in table 2	
Time $(t_P)^{**}$ within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds	
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.	
Time 25°C to peak temperature	6 minutes max.	8 minutes max.	
* Tolerance for peak profile Temperature (T _p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t _p) is defined as a supplier minimum and a user maximum.			

Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm ³ 3350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process - Classification Temperatures (Tc)

Package	Volume mm ³	Volume mm ³	Volume mm ³
Thickness	<350	350-2000	>2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ Tjmax
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ Tjmax
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
ТСТ	JESD-22, A104	500 Cycles, -65°C~150°C



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